

Abstract Submitted
for the SES21 Meeting of
The American Physical Society

Intrinsic optical absorption and d.c. conductivity in Dirac metals¹

ADAMYA GOYAL, Department of Physics, University of Florida, PRACHI SHARMA, School of Physics and Astronomy, University of Minnesota, DMITRII MASLOV, Department of Physics, University of Florida — In an ideal Dirac metal, optical absorption is absent for frequencies below the Pauli threshold (twice the Fermi energy). In real systems, however, e.g., in doped graphene, both optical absorption [1] and Raman scattering [2] find a very broad transition region around the Pauli threshold. While a number of extrinsic damping mechanisms were proposed to explain this observation in the past, we argue that the effect can be explained by an intrinsic mechanism – Auger-like recombination of optically excited minority carriers with equilibrium majority carriers. The idea goes back to a similar mechanism proposed for doped gapped semiconductors by Gavoret et al [3]. The width of the transition region in this mechanism is comparable to the Fermi energy. We also discuss certain electron-hole processes that give a scaling to the d.c. conductivity and could possibly be detected in 3-dimensional Dirac systems.

[1] Li, Z., et al. *Nature Phys.* 4, 532–535 (2008)

[2] E. Riccardi, et al. *Phys. Rev. Lett.* 116, 066805 (2016)

[3] J. Gavoret, et al. *Journal de Physique*, 1969, 30 (11-12), pp.987-997.

¹National Science Foundation under Grant No. NSF DMR-1720816

Adamyia Goyal
University of Florida

Date submitted: 30 Sep 2021

Electronic form version 1.4